



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

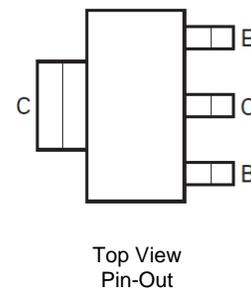
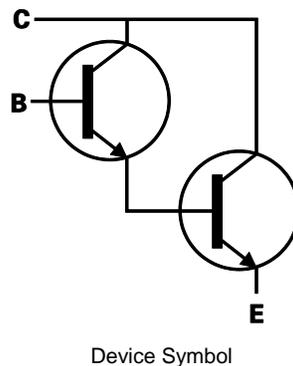
- $BV_{CEO} > 100V$
- $BV_{CBO} > 100V$
- $I_C = 1.5A$ High Continuous Current
- $h_{FE} > 10k$ for very High Gain @100mA

Mechanical Data

- Case: SOT223
- Case material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.112 grams (Approximate)

Applications

- Lamp
- Relay
- Solenoid Driving



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

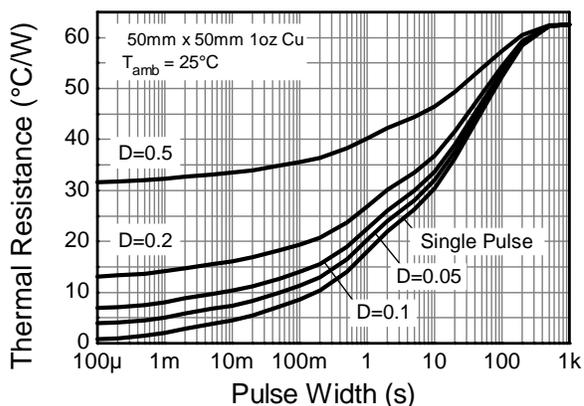
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	12	V
Continuous Collector Current	I _C	1.5	A
Peak Pulse Current	I _{CM}	2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

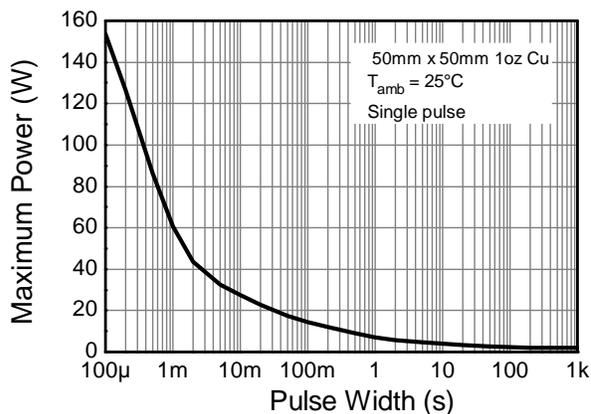
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1	W
Power Dissipation (Note 6)	P _D	1.25	W
Power Dissipation (Note 7)	P _D	2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	125	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	100	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	62	°C/W
Thermal Resistance, Junction to Lead (Note 8)	R _{θJL}	19.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
5. For a device surface mounted on 15mm x 14mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as Note 5, except the device is surface mounted on 25mm x 25mm with 1oz copper.
 7. Same as Note 5, except the device is surface mounted on 50mm x 50mm with 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

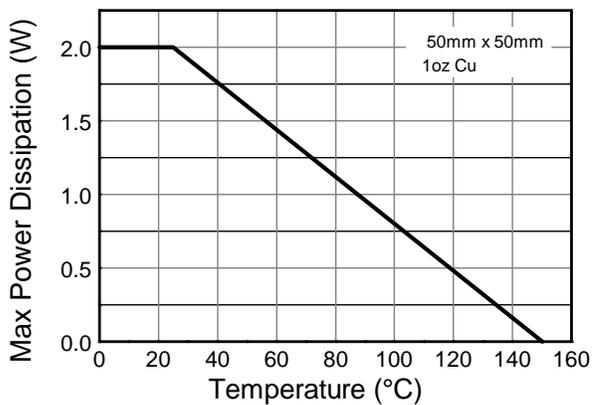
Thermal Characteristics and Derating Information



Transient Thermal Impedance



Pulse Power Dissipation



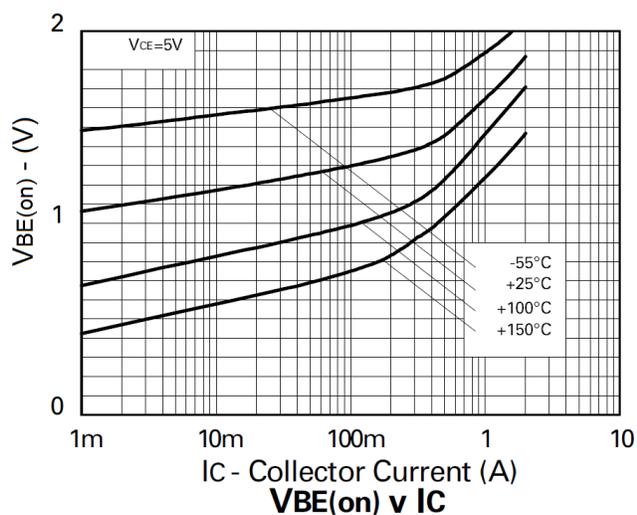
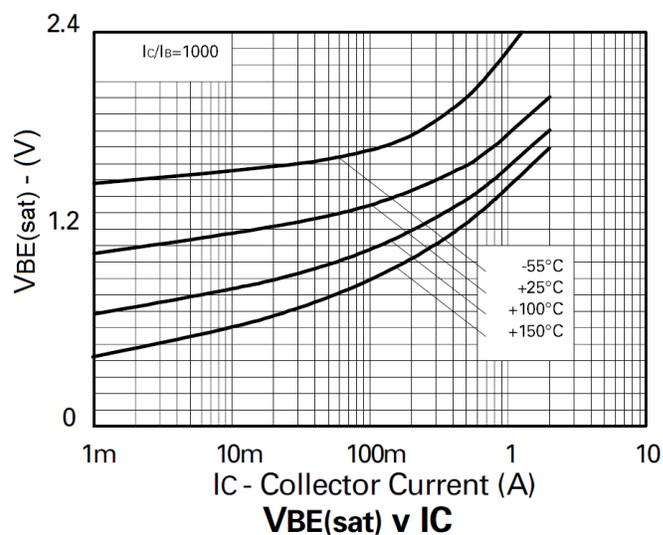
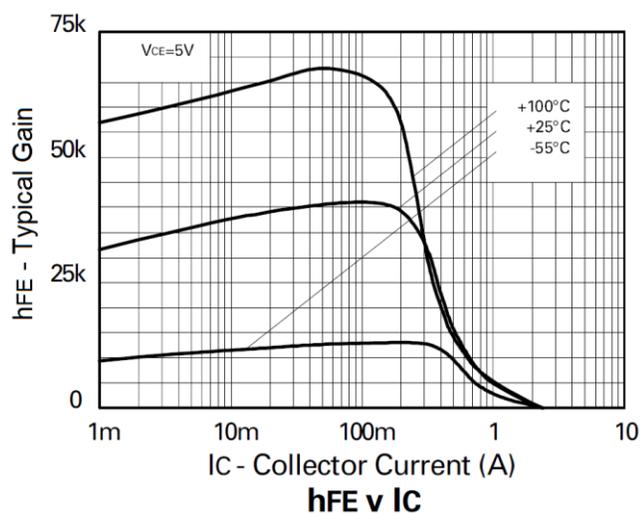
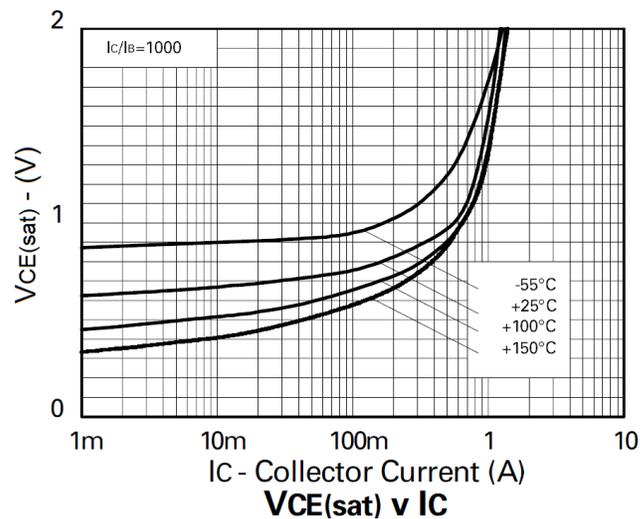
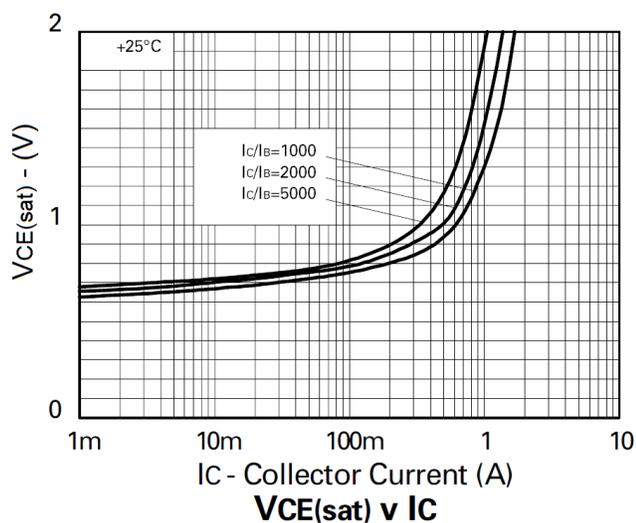
Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

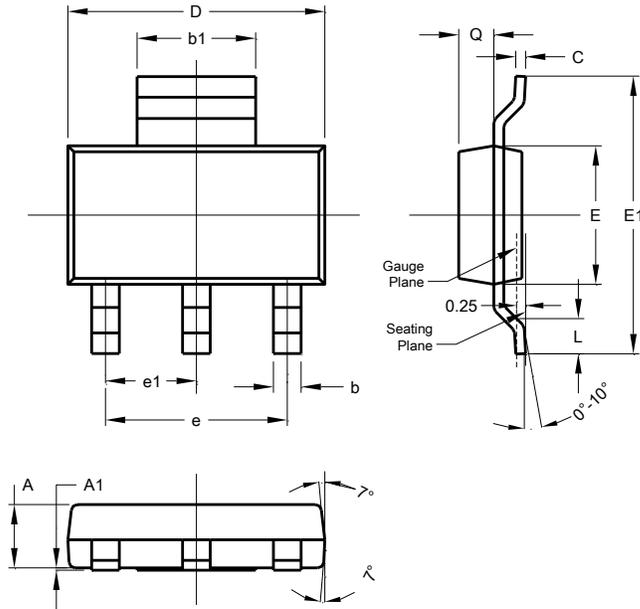
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	100	300	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	100	130	-	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	12	14	-	V	$I_E = 100\mu A$
Collector-Base Cut-Off Current	I_{CBO}	-	<10	100	nA	$V_{CB} = 80V$
Collector-Emitter Cut-Off Current	I_{CES}	-	<10	200	nA	$V_{CE} = 80V$
Emitter Cut-Off Current	I_{EBO}	-	<10	100	nA	$V_{EB} = 7V$
DC Current Gain (Note 9)	h_{FE}	10,000 1,000	-	-	-	$I_C = 100mA, V_{CE} = 5V$ $I_C = 1A, V_{CE} = 5V$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	-	-	1.5	V	$I_C = 100mA, I_B = 0.1mA$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	-	-	2.0	V	$I_C = 100mA, V_{CE} = 5V$
Output Capacitance (Note 9)	C_{obo}	-	6.0	8.0	pF	$V_{CB} = 10V, f = 1MHz$
Current Gain-Bandwidth Product (Note 9)	f_T	200	-	-	MHz	$V_{CE} = 5V, I_C = 100mA$
Turn-On Time	t_{on}	-	0.7	-	μs	$V_{CC} = 10V, I_C = 100\mu A$
Turn-Off Time	t_{off}	-	2.5	-	μs	$I_{B1} = -I_{B2} = 0.1mA$

Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

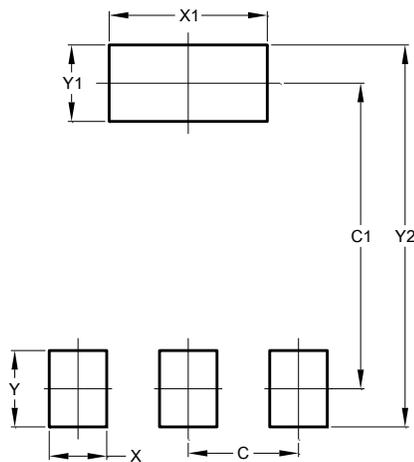


Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00